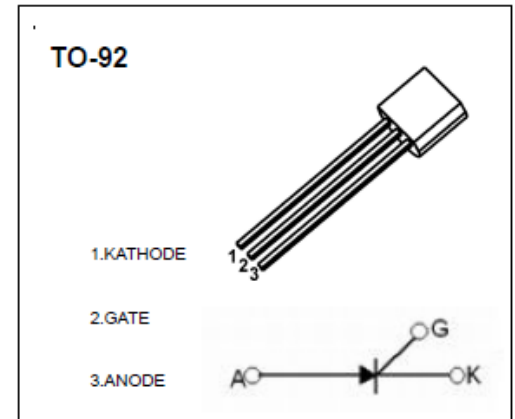


TO-92 Plastic-Encapsulate Thyristors

MCR100- 6,- 8 Silicon Controlled Rectifier

MAIN FEATURES

Symbol	value	unit
$I_{T(RMS)}$	0.8	A
V_{DRM} / V_{RRM}	MCR100-6	400
	MCR100-8	600
T_j	Junction Temperature	-40 ~ 125 °C
T_{stg}	Storage Temperature	-55 ~ 150 °C



DESCRIPTION

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

FEATURES

- Blocking voltage to 400 V (MCR100-6)
- RMS on-state current to 0.8 A
- General purpose switching

APPLICATIONS

- General purpose switching
- Phase control applications
- Solid state relays

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit	
On state voltage *	V_{TM}	$I_{TM}=1A$		1.7	V	
Gate trigger voltage	V_{GT}	$V_{AK}=7V$		0.8	V	
Peak Repetitive forward and reverse blocking voltage	V_{DRM}/V_{RRM}	$I_{DRM}/I_{RRM}= 10 \mu A$	400		V	
MCR100-6 MCR100-8			600			
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}	$V_{AK}= \text{Rated}$ V_{DRM} or V_{RRM}		10	μA	
Holding current	I_H	$I_{HL}=20mA, V_{AK}=7V$		5	mA	
Gate trigger current	I_{GT}	$V_{AK}=7V$	A1	10	30	μA
			A	30	80	μA
			B	80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.